

N-Channel 40V (D-S) Power MOSFET

Features

- 100% Avalanche Tested
- Extremely Low Losses with Low FOM Rdson*Qg
- RoHS Compliant, Halogen Free, Pb-Free
- AEC-Q101 Qualified
- MSL 1

Applications

- Automotive systems
- Synchronous Rectification in SMPS
- Hard Switching and High Speed Circuit

Absolute Maximum Ratings (TJ=25°C unless otherwise noted)							
Parameter	Symbol	Value	Unit				
Drain Source Voltage	V _{DS}	40	V				
Gate Source Voltage	V _{GS}	±20	V				
Drain Current, Continuous V _{GS} =10V <i>(Note 1)</i>	T _C =25°C	1	180	٨			
	T _C =100°C	- I _D	107	A			
Drain Current, Pulsed (Note 2)	I _{DM}	720	А				
Single Avalanche Energy @ L=0.3mH		E _{AS}	590	mJ			
Power Dissipation(Note 3)	T _C =25°C	PD	290	W			
Operating Junction/ Storage Temperat	TJ/ T _{STG}	-55 to +150	°C				

Note 1: Calculated continuous current based on maximum allowable junction temperature. Note 2: Repetitive rating; pulse width limited by max. junction temperature.

Thermal Characteristics			
Parameter	Symbol	Мах	Unit
Thermal Resistance Junction to Case(Note 3)	R _{thJC}	0.43	°C/W

Note 3: The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.



11

10

9 10 11

1 G C



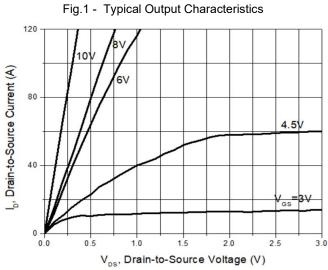
Electrical Characteristics (T _J =25°C unless otherwise noted)								
Parameter	Symbol	bol Test Conditions		Тур	Мах	Unit		
Drain Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250µA	40			V		
Zero Gate Voltage Drain Current	IDSS	V _{DS} =40V, V _{GS} =0V			1	uA		
Gate Threshold Voltage	V _{GS(TH)}	V_{DS} = V_{GS} , I_{DS} =250uA	2		4	V		
Gate Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V			±100	nA		
Drain-Source On-state Resistance	R _{DS(on)}	V _{GS} =10V, I _D =40A		1.6	3	mΩ		
Total Gate Charge	Qg	1 - 204		135				
Gate Source Charge	Q _{gs}	I _D = 20A, V _{DS} =20V, V _{GS} = 10V		25		nC		
Gate Drain Charge	Q _{gd}	V _{GS} – 10V		35				
Turn-on Delay Time	t _{d(on)}			32				
Turn-on Rise Time	tr	 V _{GS} =10V, V _{DD} =20V,		31				
Turn-off Delay Time	t _{d(off)}	R _{GEN} =3.6Ω, R _L =1Ω		68		ns		
Turn-off Fall Time	t _f			23				
Input Capacitance	C _{iss}			10547				
Output Capacitance	pacitance C _{oss} V _{GS=} 0V, V _{DS} =30V, f=1MHz			654		pF		
Reverse Transfer Capacitance	C _{rss}			553				

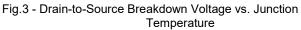
Reverse Diode Characteristics (T _J =25°C unless otherwise noted)								
Parameter Symbol		Test Conditions	Min	Тур	Max	Unit		
Continuous Source Current (Body Diode)	ls	T _c =25°C			180	A		
Pulsed Source Current (Body Diode)	I _{SM}	1c-25 C			720	A		
Diode Forward Voltage	V _{SD}	I _S =40A, V _{GS} =0V			1.2	V		
Reverse Recovery Time	T _{rr}	T _C =25°C, I _F =20A,		50		ns		
Reverse Recovery Charge	Qrr	di/dt = 100 A/µs		75		nC		

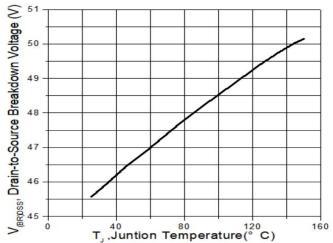


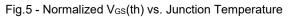
GMN03004LL GOOD-ARK Electronics

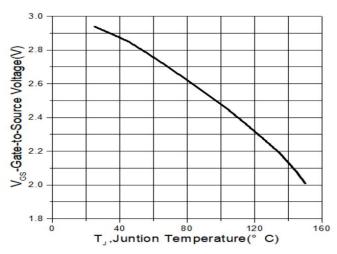
Typical Characteristics Curves (T_J = 25°C unless otherwise noted)











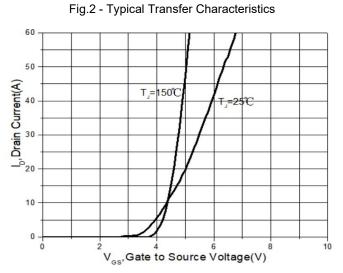


Fig.4 - Normalized On-Resistance vs. Junction Temperature

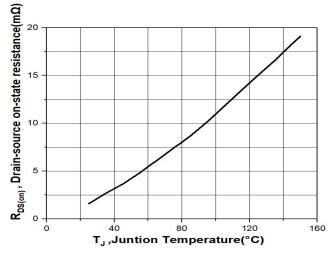
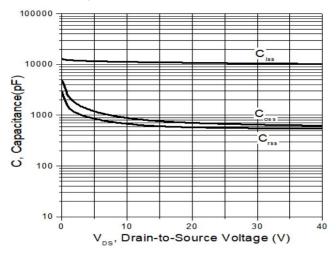


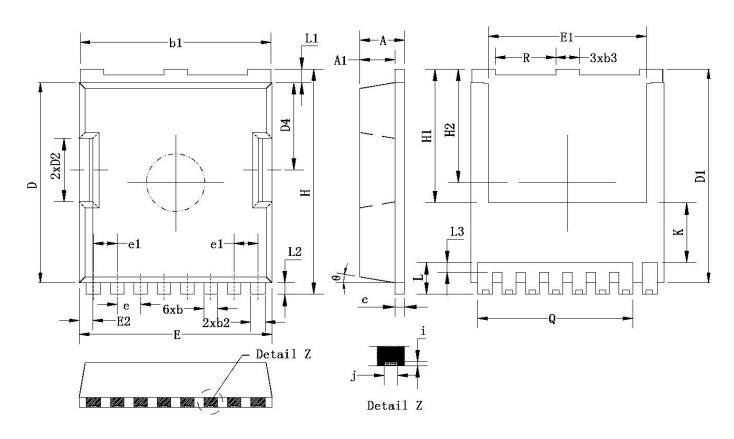
Fig.6 - Capacitance Characteristics





Package Outline Dimensions (Unit: millimeters)

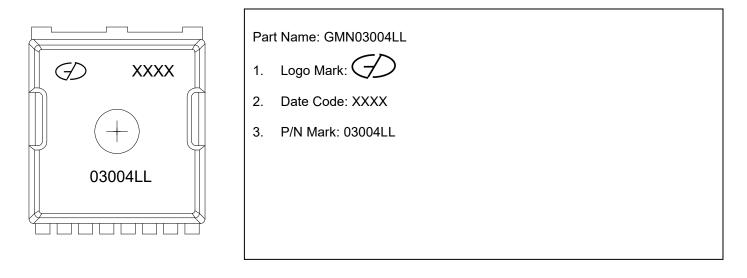




Symbol	Min	Тур	Max	Symbol	Min	Тур	Max	
А	2.25	2.30	2.35	E2	0.65	0.70	0.75	
A1	1.75	1.80	1.85	Н	11.60	11.70	11.80	
b	0.65	0.70	0.75	H1		6.95 BSC		
b1	9.75	9.80	9.85	H2	5.90 BSC			
b2	0.70	0.75	0.80	i	0.10 REF			
b3	1.15	1.20	1.25	j	0.35 REF			
с	0.45	0.50	0.55	K	3.10 REF			
D	10.35	10.40	10.45	L	1.55	1.65	1.75	
D1	11.00	11.10	11.20	L1	0.65	0.70	0.75	
D2	3.25	3.30	3.35	L2	0.50	0.60	0.70	
D4	4.50	4.55	4.60	L3	0.40	0.50	0.60	
e	1.20 BSC			Q	7.95 REF			
e1	1.225 BSC		R	3.05	3.10	3.15		
Е	9.85	9.90	9.95	θ	10°REF			
E1	8.00	8.10	8.20					



Marking Outline





Disclaimers

These materials are intended as a reference to assist our customers in the selection of the Suzhou Good-Ark product best suited to the customer's application; they do not convey any license under any intellectual property rights, or any other rights, belonging to Suzhou Good-Ark Electronics Co., Ltd.or a third party.

Suzhou Good-Ark Electronics Co., Ltd. assumes no responsibility for any damage, or infringement of any third-party's rights, originating in the use of any product data, diagrams, charts, programs, algorithms, or circuit application examples contained in these materials.

All information contained in these materials, including product data, diagrams, charts, programs and algorithms represents information on products at the time of publication of these materials, and are subject to change by Suzhou Good-Ark Electronics Co., Ltd. without notice due to product improvements or other reasons. It is therefore recommended that customers contact Suzhou Good-Ark Electronics Co., Ltd. for the latest product information before purchasing a product listed herein. The information described here may contain technical inaccuracies or typographical errors. Suzhou Good-Ark Electronics Co., Ltd. assumes no responsibility for any damage, liability, or other loss rising from these inaccuracies or errors. Please also pay attention to information published by Suzhou Good-Ark Electronics Co., Ltd. by various means, including our website home page. (http://www.goodark.com)

When using any or all of the information contained in these materials, including product data, diagrams, charts, programs, and algorithms, please be sure to evaluate all information as a total system before making a final decision on the applicability of the information and products. Suzhou Good-Ark Electronics Co., Ltd. assumes no responsibility for any damage, liability or other loss resulting from the information contained herein.

The prior written approval of Suzhou Good-Ark Electronics Co., Ltd. is necessary to reprint or reproduce in whole or in part these materials.

Please contact Suzhou Good-Ark Electronics Co., Ltd. or an authorized distributor for further details on these materials or the products contained herein.